

CR5AS-12

Thyristor

Medium Power Use

REJ03G0345-0200

Rev.2.00

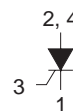
Mar.01.2005

Features

- $I_{T(AV)}$: 5 A
- V_{DRM} : 600 V
- I_{GT} : 100 μ A
- Non-Insulated Type
- Glass Passivation Type

Outline

PRSS0004ZA-A
(Package name: MP-3A)



1. Cathode
2. Anode
3. Gate
4. Anode

Applications

Switching mode power supply, regulator for auticycle, protective circuit for TV sets, VCRs, and printers, igniter for auticycle, electric tool, strobe flasher, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak reverse voltage	V_{RRM}	600	V
Non-repetitive peak reverse voltage	V_{RSM}	720	V
DC reverse voltage	$V_{R(DC)}$	480	V
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
DC off-state voltage ^{Note1}	$V_{D(DC)}$	480	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	7.8	A	
Average on-state current	$I_{T(AV)}$	5	A	Commercial frequency, sine half wave 180° conduction, $T_C = 88^\circ\text{C}$
Surge on-state current	I_{TSM}	90	A	60Hz sine half wave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	33	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	0.5	W	
Average gate power dissipation	$P_{G(AV)}$	0.1	W	
Peak gate forward voltage	V_{FGM}	6	V	
Peak gate reverse voltage	V_{RGM}	6	V	
Peak gate forward current	I_{FGM}	0.3	A	
Junction temperature	T_J	- 40 to +125	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 40 to +125	$^\circ\text{C}$	
Mass	—	0.26	g	Typical value

Notes: 1. With gate to cathode resistance $R_{GK} = 220 \Omega$.

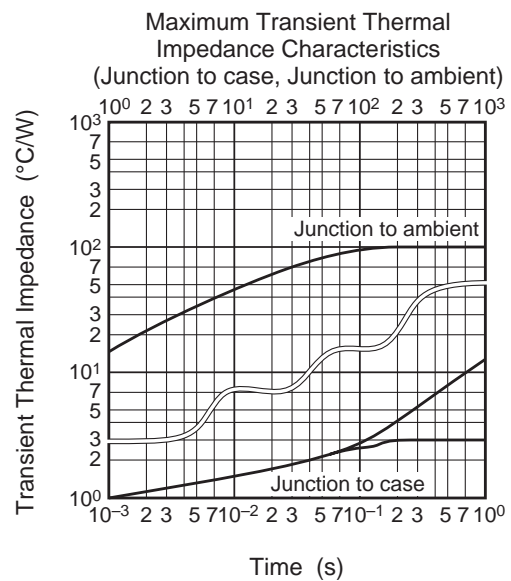
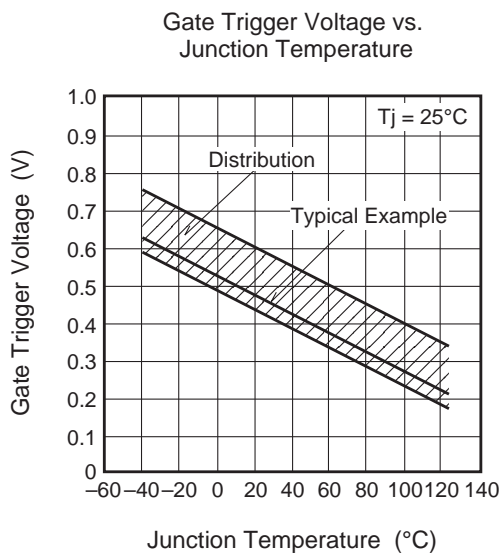
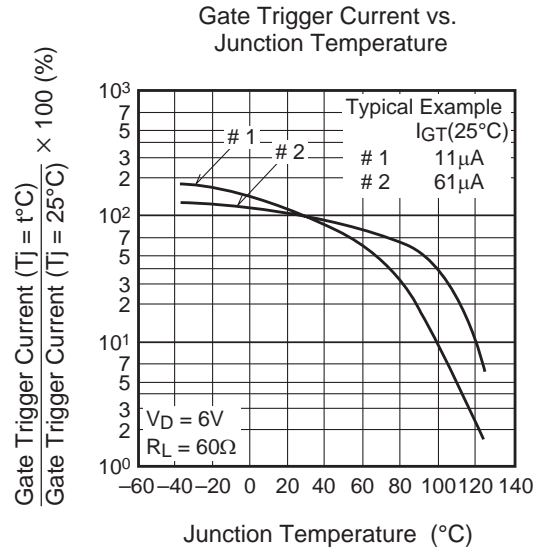
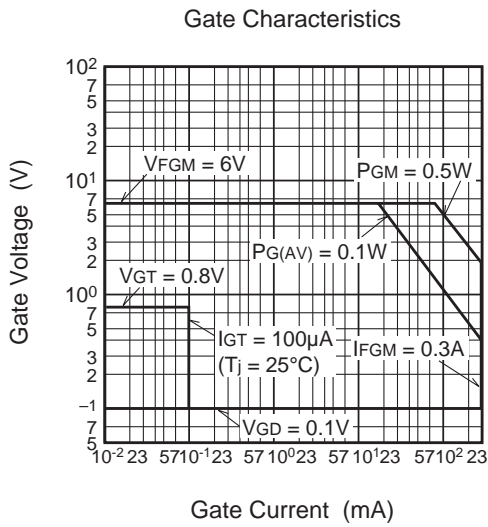
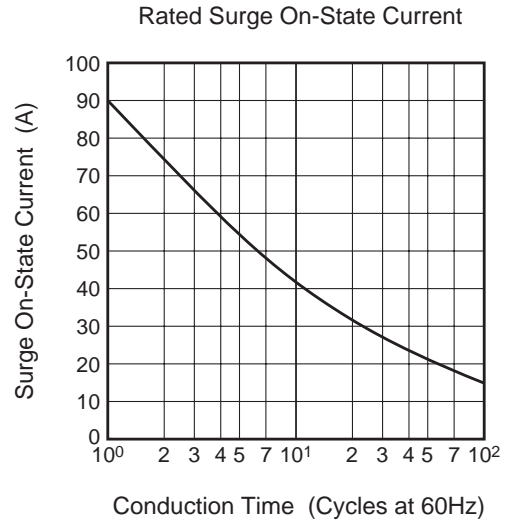
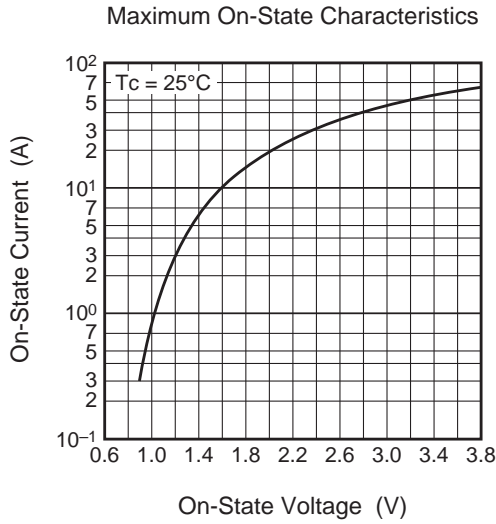
Electrical Characteristics

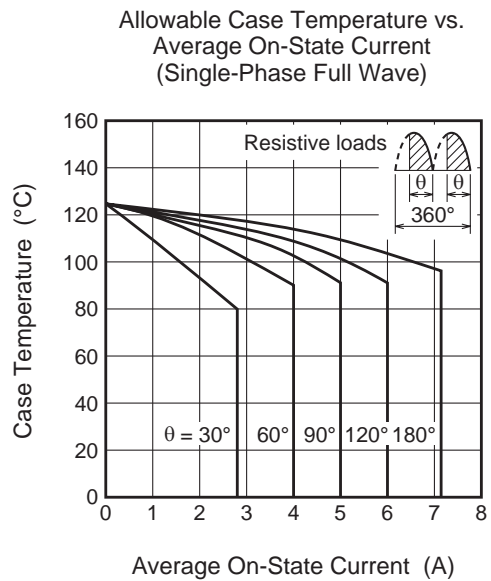
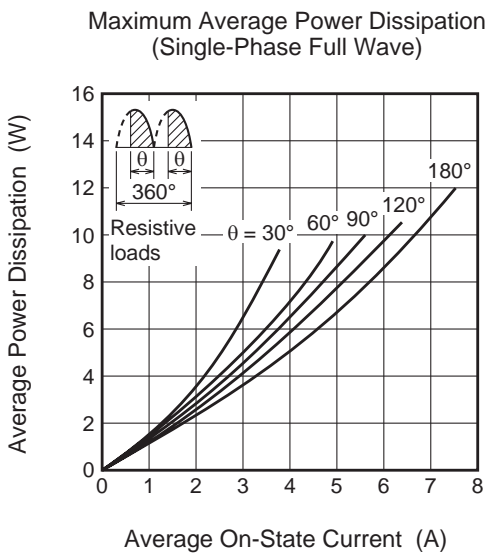
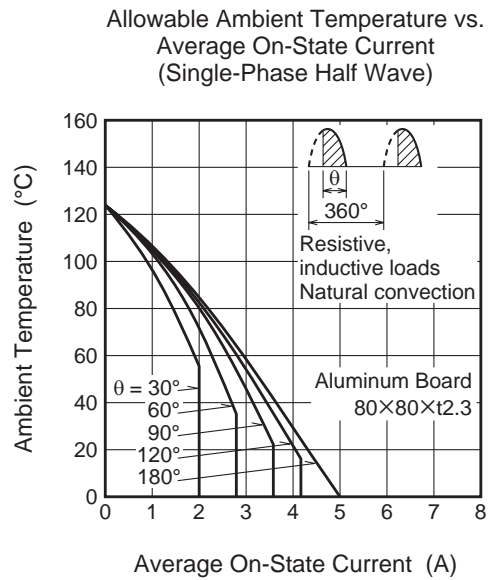
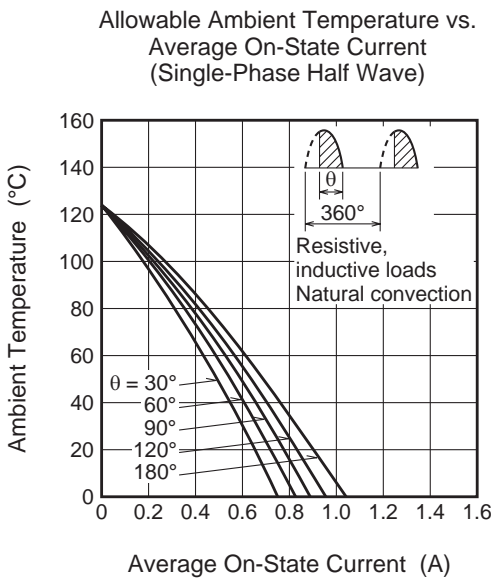
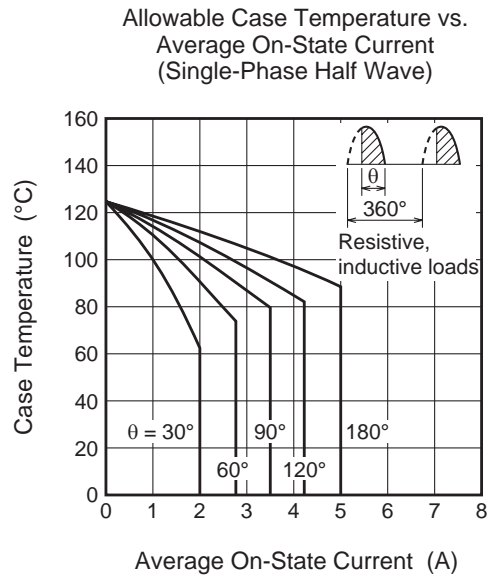
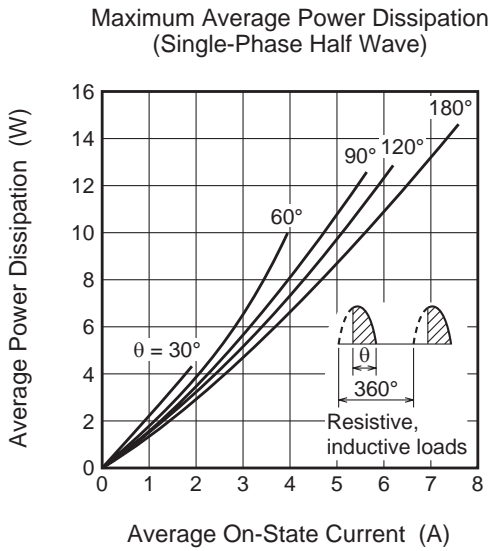
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak reverse current	I_{RRM}	—	—	2.0	mA	$T_J = 125^\circ\text{C}$, V_{RRM} applied, $R_{GK} = 220 \Omega$
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_J = 125^\circ\text{C}$, V_{DRM} applied, $R_{GK} = 220 \Omega$
On-state voltage	V_{TM}	—	—	1.8	V	$T_C = 25^\circ\text{C}$, $I_{TM} = 15 \text{ A}$, instantaneous value
Gate trigger voltage	V_{GT}	—	—	0.8	V	$T_J = 25^\circ\text{C}$, $V_D = 6 \text{ V}$, $I_T = 0.1 \text{ A}$
Gate non-trigger voltage	V_{GD}	0.1	—	—	V	$T_J = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$, $R_{GK} = 220 \Omega$
Gate trigger current	I_{GT}	1	—	100 ^{Note3}	μA	$T_J = 25^\circ\text{C}$, $V_D = 6 \text{ V}$, $I_T = 0.1 \text{ A}$
Holding current	I_H	—	3.5	—	mA	$T_J = 25^\circ\text{C}$, $V_D = 12 \text{ V}$, $R_{GK} = 220 \Omega$
Thermal resistance	$R_{th(j-c)}$	—	—	3.0	$^\circ\text{C/W}$	Junction to case ^{Note2}

Notes: 2. The measurement point for case temperature is at anode tab.

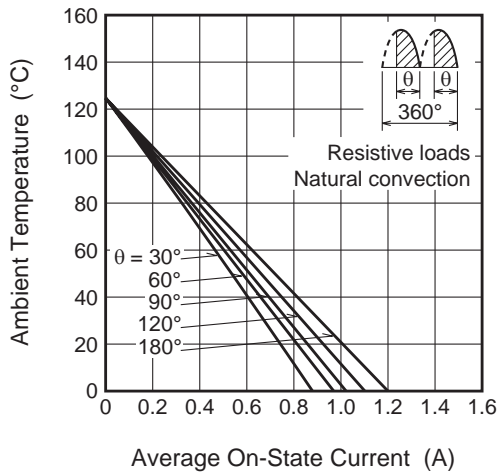
3. If special value of I_{GT} is required, I_{GT} from 20 to 100 μA is possible. (I_{GT} item: E)

Performance Curves

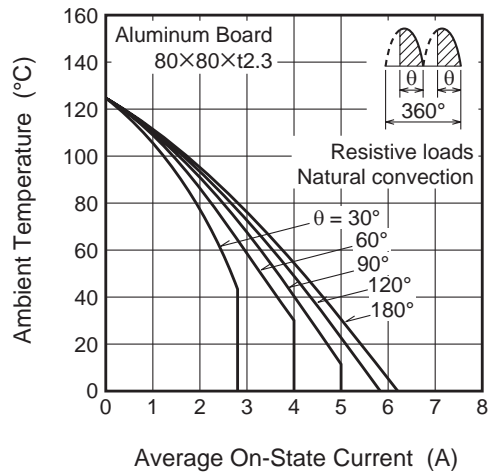




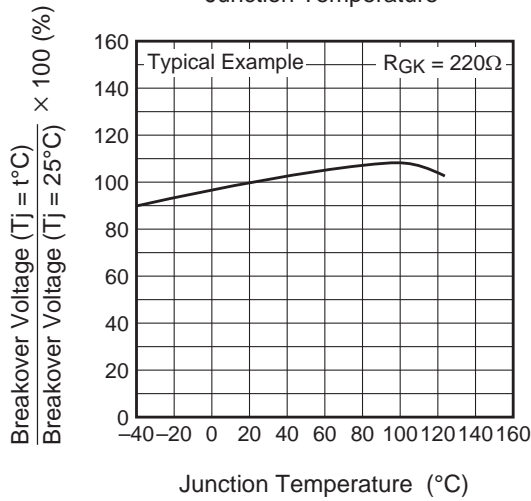
Allowable Ambient Temperature vs. Average On-State Current (Single-Phase Full Wave)



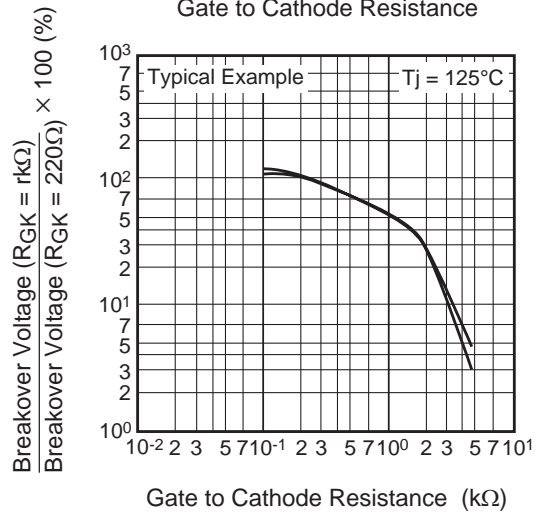
Allowable Ambient Temperature vs. Average On-State Current (Single-Phase Full Wave)



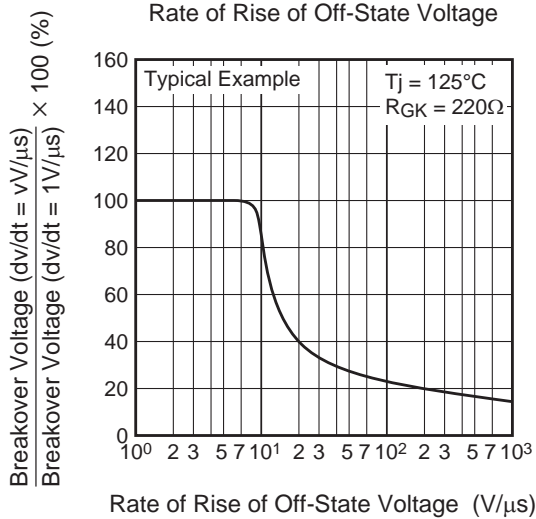
Breakover Voltage vs. Junction Temperature



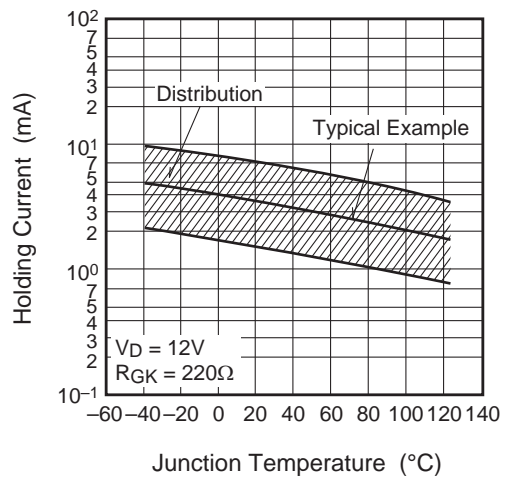
Breakover Voltage vs. Gate to Cathode Resistance

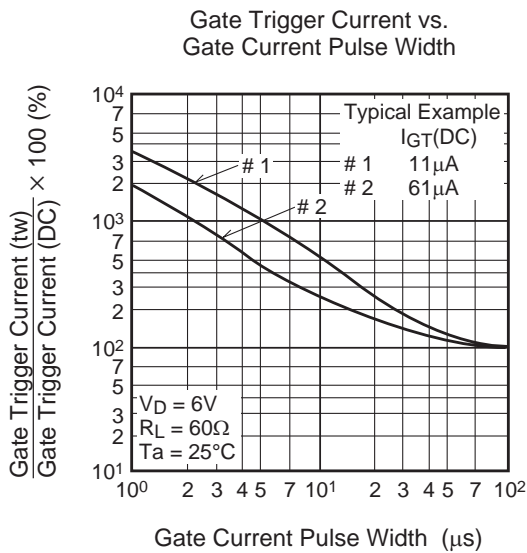
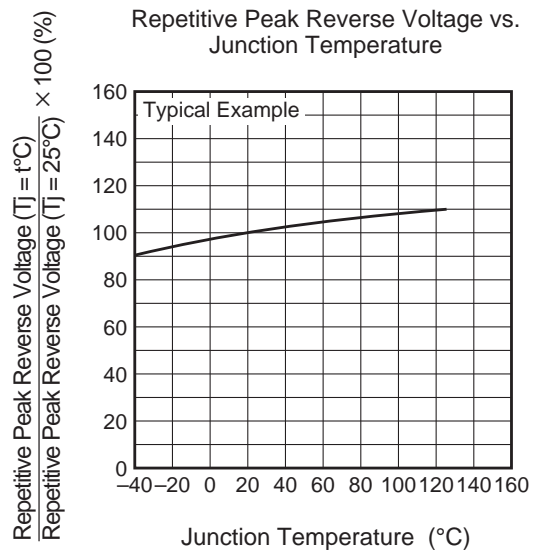
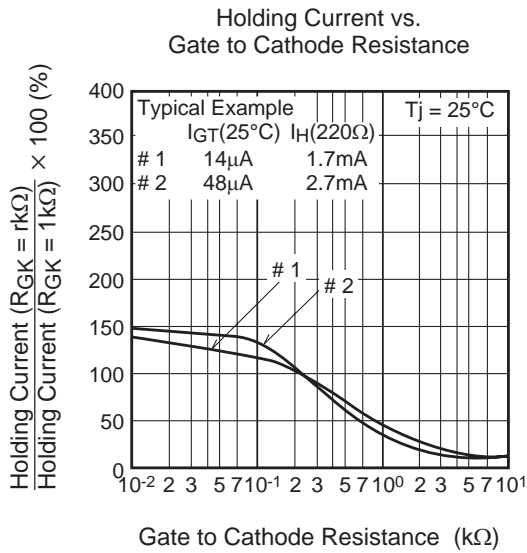


Breakover Voltage vs. Rate of Rise of Off-State Voltage

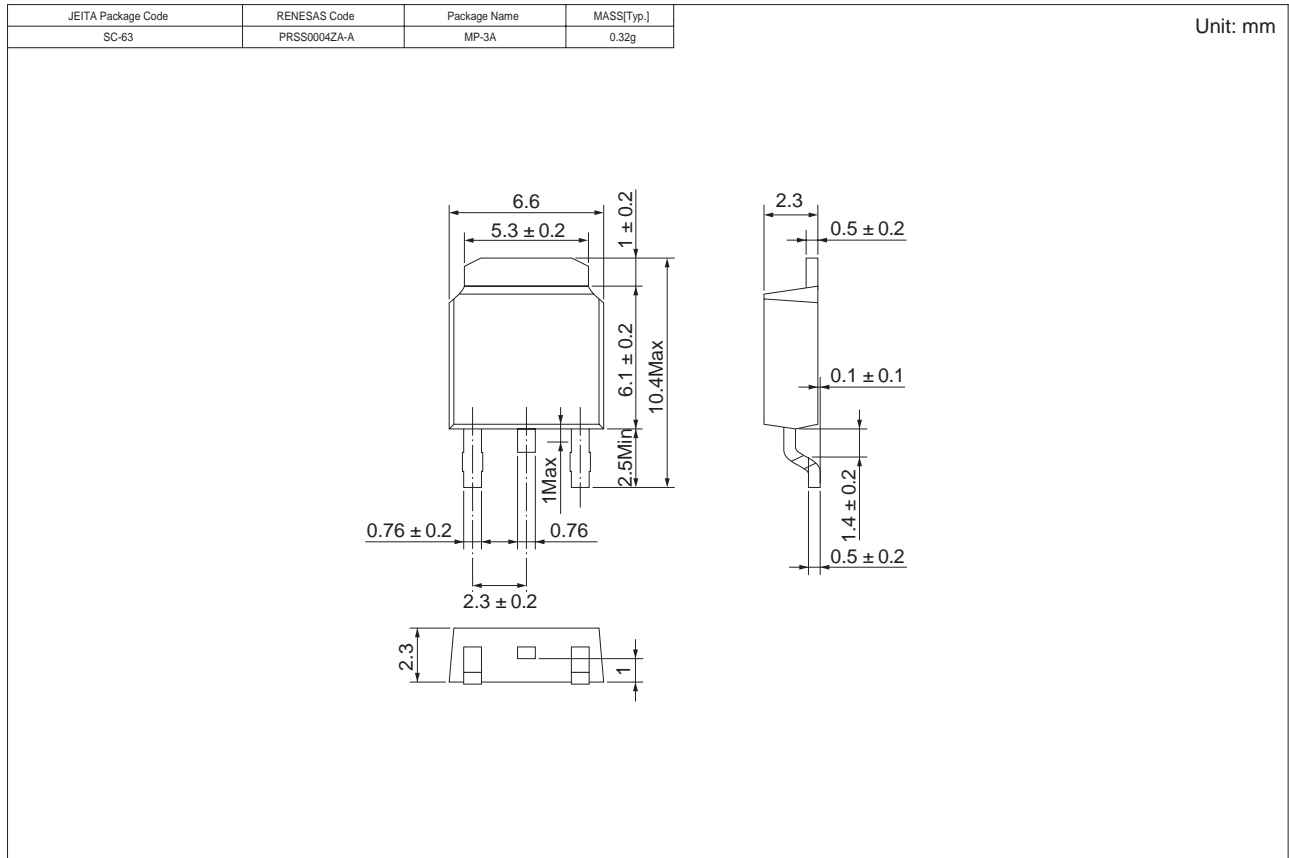


Holding Current vs. Junction Temperature





Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	CR5AS-12-T13
Surface-mounted type	Tube	75	Type name	CR5AS-12

Note : Please confirm the specification about the shipping in detail.

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